

In the specification

Please amend paragraph 0024 as follows:

0024 An example is now described that illustrates in particular the advantageousness of the invention as compared to the prior art. The common process window for a 130-nanometer (nm) trench through all pitches is to be maximized. However, for sake of illustrative[ly] clarity, only 240-nm and 1000-nm pitches are considered. For a trench of 1000-nm pitch, 100-nm ASB's at a distance (center-to-center) of 270 nm are added. The CD specification is +/- 10%, such that the allowable CD is between 117 nm and 143 nm. If the CD on mask is 130 nm, then the process window for the trench of the 240-nm pitch is shown in FIG. 5. The intensity threshold, related to exposure, at the process window center is 0.36. To align the process window of a more-isolated trench, such as the trench having a 1000-nm pitch, the CD should be biased from 130 nm to 144 nm. In this case, the process window for such a 1000-nm pitch trench is shown in FIG. 6. The intensity threshold at the process window center is also 0.36, and the common process window of the two pitches is maximized, as is shown in FIG. 7.